

IDS 12/12/2003

Form PTO-1449 - U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE		Atty. Docket No. YOR919970121US2 (16323A)	Serial N. 10/735,167 considered
LIST OF PRIOR ART CITED BY APPLICANT		Applicant Frank Cardone, et al.	
(Use several sheets if necessary)		Filing Date Herewith	Group considered 2822

U.S. PATENT DOCUMENTS

EXAMINER INITIAL*		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FLING DATE (if appropriate)
KBD	AA	5,316,958	5/31/1994	Meyerson			
	AB	5,628,834	5/13/1997	Copel et al.			
		5,047,365	9/10/1991	Kawanaka et al.			
		5,241,197	8/31/1993	Murakami et al.			
		5,298,452	3/29/1994	Meyerson			
		5,089,428	2/18/1992	Verret et al.			
		5,616,515	4/1/1997	Okuno			
		5,607,511	3/4/1997	Meyerson			
		5,181,964	1/20/1993	Meyerson			
↓		5,227,644	7/1993	Ueno			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
KBD		494,395	7/15/1992	Europe				
		2-288328	11/28/1998	Japan				
		63-168021	7/12/1988	Japan				
↓		6,061,489	3/4/1994	Japan				

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

KBD		Sheldon P. et al. (1986) "Growth, Nucleation, and Electrical properties of Molecular Beam Epitaxially grown, As-doped Ge on Si Substrates" J. Vac. Sci & Tech. A, Vol. 4, No. 3, pt. 1, pgs. 889-893;
		Ismail K. et al (1992) "High Transconductance n-type Si/SiGe Modulation-Doped Field-Effect Transistors" IEEE Electron Device Letters, Vol. 13, No. 5, pgs. 229-231; and
↓		Ismail K. et al. (1991) High Electron Mobility in Modulation-Doped Si/SiGe" Applied Physics Letters, Vol. 58, No. 19, pgs. 2117-2119.

EXAMINER	DATE CONSIDERED
<i>Johnath. Drury</i>	6/25/2005

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.